

June 2009

2N6520 PNP Epitaxial Silicon Transistor

Features

- · High Voltage Transistor
- Collector-Emitter Voltage: V_{CBO}= -350V
- Collector Dissipation: P_C (max)=625mW
- Complement to 2N6517



Absolute Maximum Ratings* T_A = 25°C unless otherwise noted

Symbol	Parameter	Value	Unit	
V_{CBO}	Collector-Base Voltage	-350	V	
V _{CEO}	Collector-Emitter Voltage	-350 V		
V _{EBO}	Emitter-Base Voltage	-5	V	
I _C	Collector Current	-500	mA	
I _B	Base Current	-250	mA	
P _C	Collector Power Dissipation	0.625	W	
	Derate above 25°C	5	mW/°C	
T _J	Junction Temperature	150	°C	
T _{STG}	Storage Temperature	-55 to +150	°C	

Electrical Characteristics T_A =25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	I _C = -100μA, I _E =0	-350		V
BV _{CEO}	* Collector-Emitter Breakdown Voltage	I _C = -1mA, I _B =0	-350		V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E = -10μA, I _C =0	-5		V
I _{CBO}	Collector Cut-off Current	V _{CB} = -250V, I _E =0		-50	nA
I _{EBO}	Emitter Cut-off Current	V_{EB} = -4V, I_C =0		-50	nA
h _{FE}	* DC Current Gain	V_{CE} = -10V, I_{C} = -1mA V_{CE} = -10V, I_{C} = -10mA V_{CE} = -10V, I_{C} = -30mA V_{CE} = -10V, I_{C} = -50mA V_{CE} = -10V, I_{C} = -100mA	20 30 30 20 15	200 200	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I_{C} = -10mA, I_{B} = -1mA I_{C} = -20mA, I_{B} = -2mA I_{C} = -30mA, I_{B} = -3mA I_{C} = -50mA, I_{B} = -5mA		-0.30 -0.35 -0.50 -1	>>>>
V _{BE} (sat)	Base-Emitter Saturation Voltage	I_{C} = -10mA, I_{B} = -1mA I_{C} = -20mA, I_{B} = -2mA I_{C} = -30mA, I_{B} = -3mA		-0.75 -0.85 -0.90	V V V
V _{BE} (on)	Base-Emitter On Voltage	V _{CE} = -10V, I _C = -100mA		-2	V
f _T	* Current Gain Bandwidth Product	V _{CE} = -20V, I _C = -10mA, f=20MHz	40	200	MHz
C _{ob}	Output Capacitance	V _{CB} = -20V, I _E =0, f=1MHz		6	pF
C _{EB}	Emitter-Base Capacitance	V _{EB} = -0.5V, I _C =0, f=1MHz		100	pF
t _{ON}	Turn On Time	V _{BE} (off)= -2V, V _{CC} = -100V I _C = -50mA, I _{B1} = -10mA		200	ns
t _{OFF}	Turn Off Time	V _{CC} = -100V, I _C = -50mA I _{B1} =I _{B2} = -10mA		3.5	ns

^{*} Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

Typical Performance Characteristics

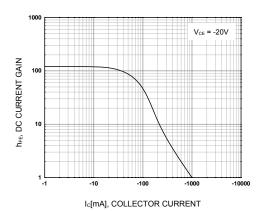


Figure 1. DC current Gain

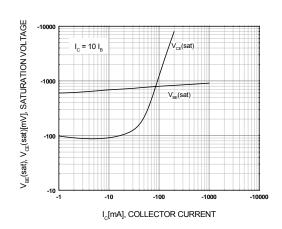


Figure 2. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

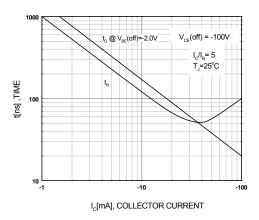


Figure 3. Turn-On Time

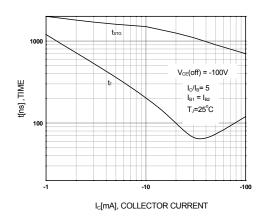


Figure 4. Turn-Off Time

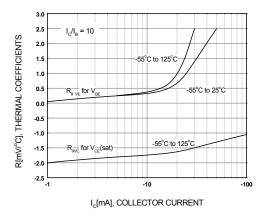


Figure 5. Temperature Coefficients

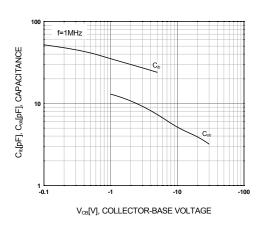


Figure 6. Capacitance

Typical Performance Characteristics

(Continued)

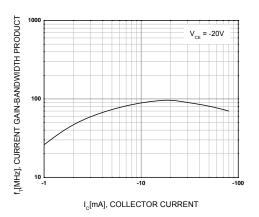
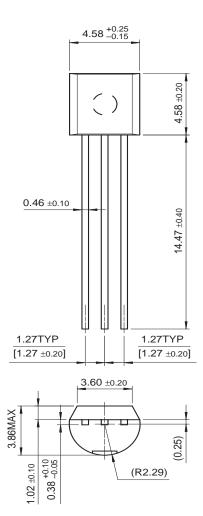
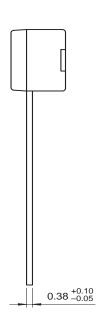


Figure 7. Current Gain Bandwidth Product

Physical Dimensions

TO-92





Dimensions in Millimeters





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Definition of Terms					
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